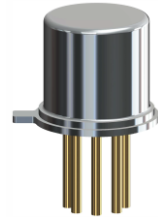
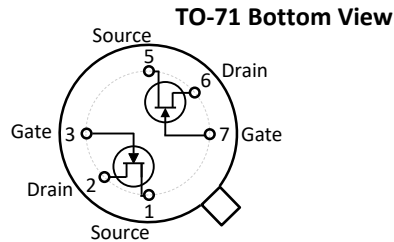


# VCR11N Dual N-Channel Voltage Controlled Resistor JFET

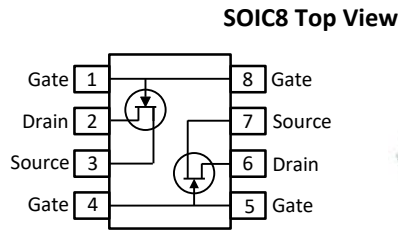
## Features

- InterFET [N0026S Geometry](#)
- Low Leakage: 10 pA Typical
- Low Input Capacitance: 6.0 pF Typical
- High Input Impedance
- RoHS Compliant
- SMT, TH, and Bare Die Package options.



## Applications

- Small Signal Attenuators
- Filters
- Amplifier Gain Control
- Oscillator Amplitude Control



## Description

The -25V InterFET VCR11N Voltage Controlled Resistor JFET are targeted for high input impedance applications. Gate leakages are less than 10pA at room temperatures. The resistance range of the VCR11N is 70 Ohms to 200 Ohms. The TO-71 package is hermetically sealed and suitable for military applications.

## Product Summary

Parameters	VCR11N Min	Unit
$BV_{GSS}$ Gate to Source Breakdown Voltage	-25	V
$V_{GS(off)}$ Gate to Source Cutoff Voltage	-8	V
$r_{ds(on)}$ Drain to Source ON Resistance	70	$\Omega$

## Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
VCR11N	Through-Hole	TO-71	Bulk
SMPVCR11N	Surface Mount	SOIC8	Bulk
SMPVCR11NTR	7" Tape and Reel: Max 500 Pieces 13" Tape and Reel: Max 2500 Pieces	SOIC8	Minimum 500 Pieces Tape and Reel
VCR11NCOT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
VCR11NCFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



**Disclaimer:** It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

## Electrical Characteristics

### Maximum Ratings (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified)

Parameters	Value	Unit
$V_{RGS}$ Reverse Gate Source and Gate Drain Voltage	-15	V
$I_{FG}$ Continuous Forward Gate Current	10	mA
$P_D$ Continuous Device Power Dissipation	300	mW
$P$ Power Derating	2.4	mW/ $^\circ\text{C}$
$T_J$ Operating Junction Temperature	-55 to 125	$^\circ\text{C}$
$T_{STG}$ Storage Temperature	-65 to 150	$^\circ\text{C}$

### Static Characteristics (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified)

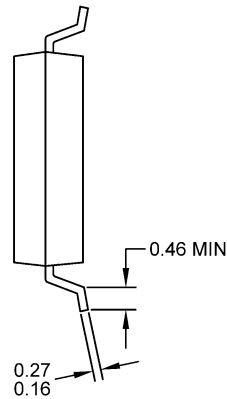
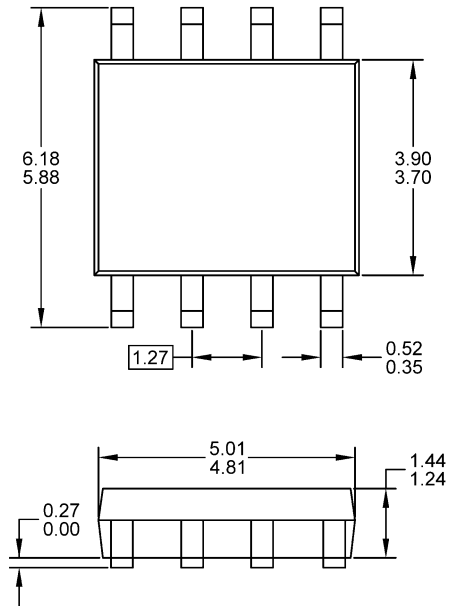
Parameters	Conditions	VCR11N		Unit
		Min	Max	
$V_{(BR)GSS}$ Gate to Source Breakdown Voltage	$I_G = -1\mu\text{A}, V_{DS} = 0\text{V}$	-25		V
$I_{GSS}$ Gate to Source Reverse Current	$V_{GS} = -15\text{V}, V_{DS} = 0\text{V}$		-0.2	nA
$V_{GS(OFF)}$ Gate to Source Cutoff Voltage	$V_{DS} = -10\text{V}, I_D = 1\mu\text{A}$	-8	-12	V
$r_{DS(MIN)}$ Static Drain to Source	Min: $V_{DS} = 100\text{mV}, r_{DS1} = 200\Omega$	0.95	1	-
$r_{DS(MAX)}$ ON Resistance Ratio	Max: $V_{GS1} = V_{GS2}, r_{DS2} = 2\text{k}\Omega$	0.95	1	-

### Dynamic Characteristics (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified)

Parameters	Conditions	VCR11N		Unit
		Min	Max	
$r_{ds(on)}$ Drain to Source ON Resistance	$I_D = 0\text{A}, V_{GS} = 0\text{V}, f = 1\text{kHz}$	70	200	$\Omega$
$C_{dg}$ Drain Gate Capacitance	$V_{DG} = 10\text{V}, I_S = 0\text{A}, f = 1\text{MHz}$		7.5	pF
$C_{sg}$ Source Gate Capacitance	$V_{GS} = 10\text{V}, I_D = 0\text{A}, f = 1\text{MHz}$		7.5	pF

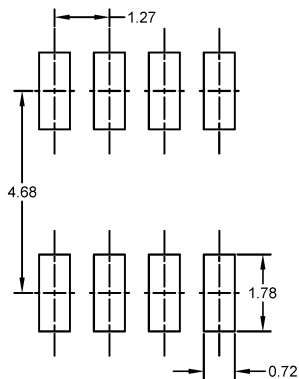
## SOIC8 Mechanical and Layout Data

### Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.21 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

### Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.